

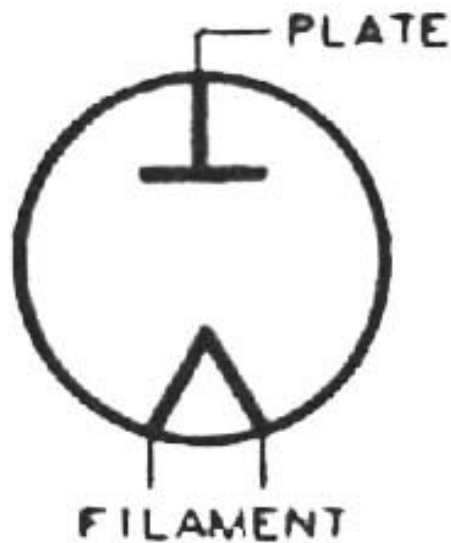
Diode in historisch perspectief

Hans Wallinga
Emeritus Universiteit Twente

Vacuüm Diode

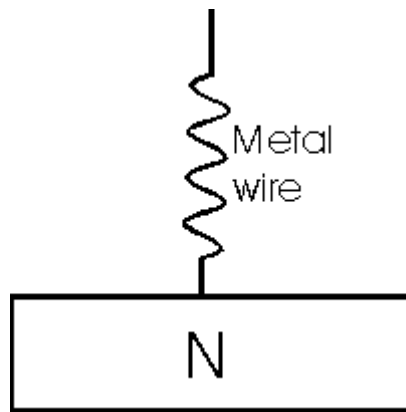
Gepatenteerd in 1904

John Ambrose Fleming
(1848-1945)

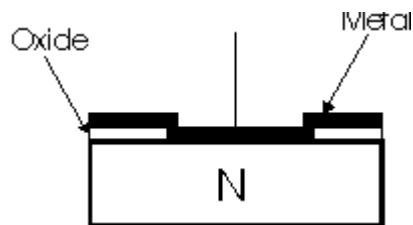


Schottky diode

Gepatenteerd in 1938



**Walter Schottky
(1886-1976)**



Nobelprijs 1911



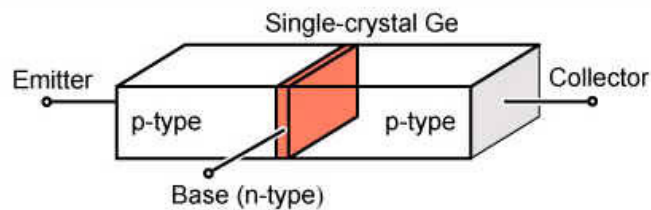
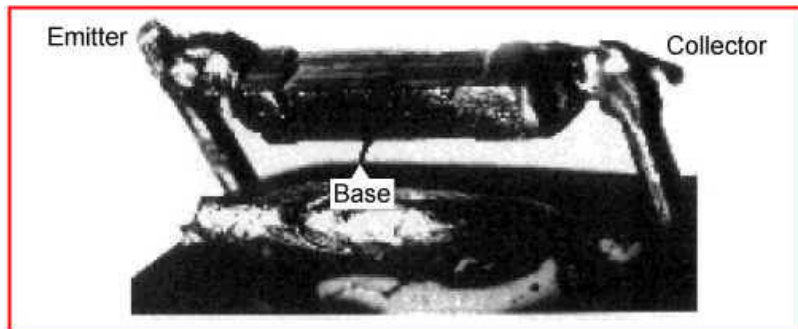
pn-overgang

Gepatenteerd in 1951

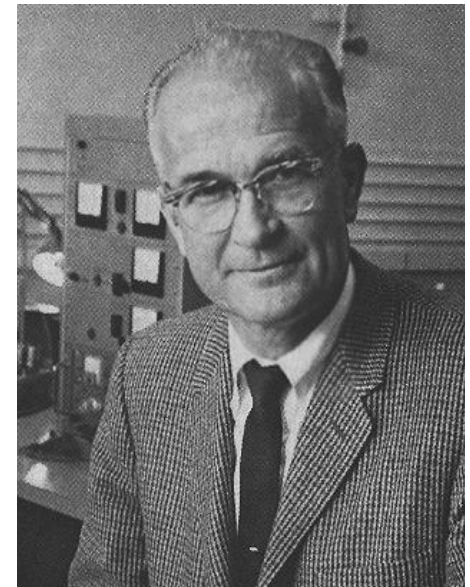
William Bradford Shockley
(1910 - 1989)

The First Junction Transistor

First transistor with diffused pn junctions by William Shockley
Bell Laboratories, Murray Hill, New Jersey (1949)



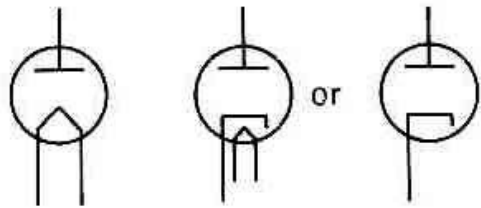
Nobelprijs 1956



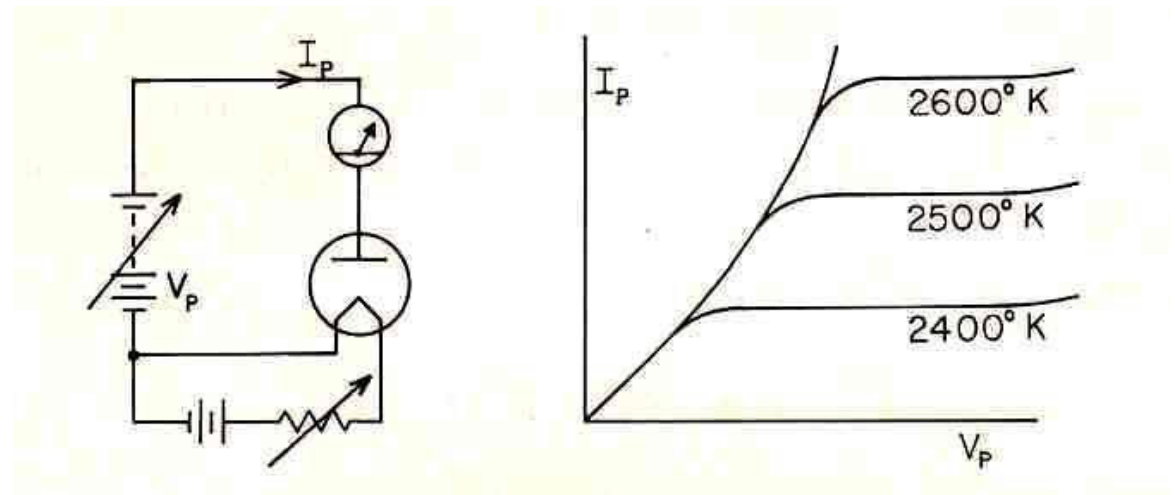
Fysische werking vacuüm diode

Thermische emissie: $J = A_0 T^2 e^{-W/kT}$

Diode stroom: $I = KV_p^{3/2}$

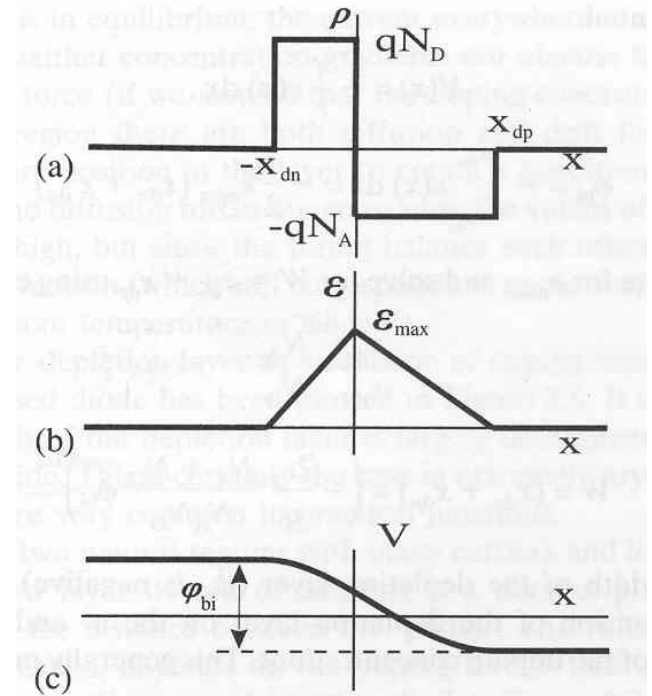
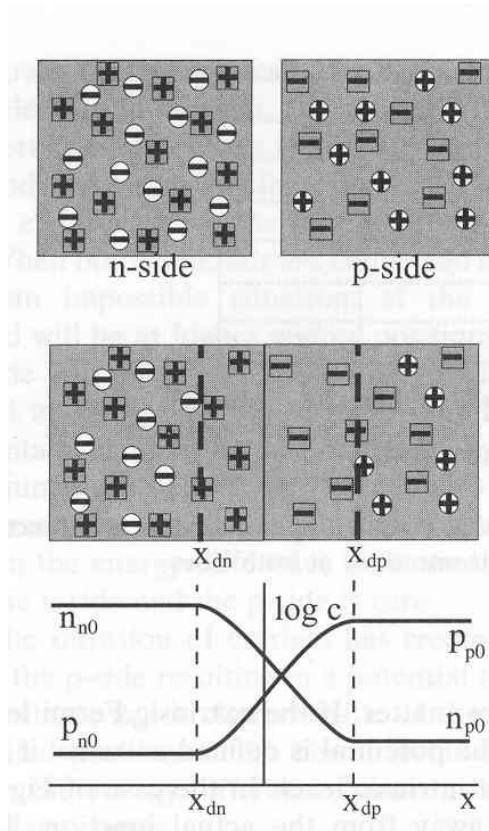


Diode symbolen



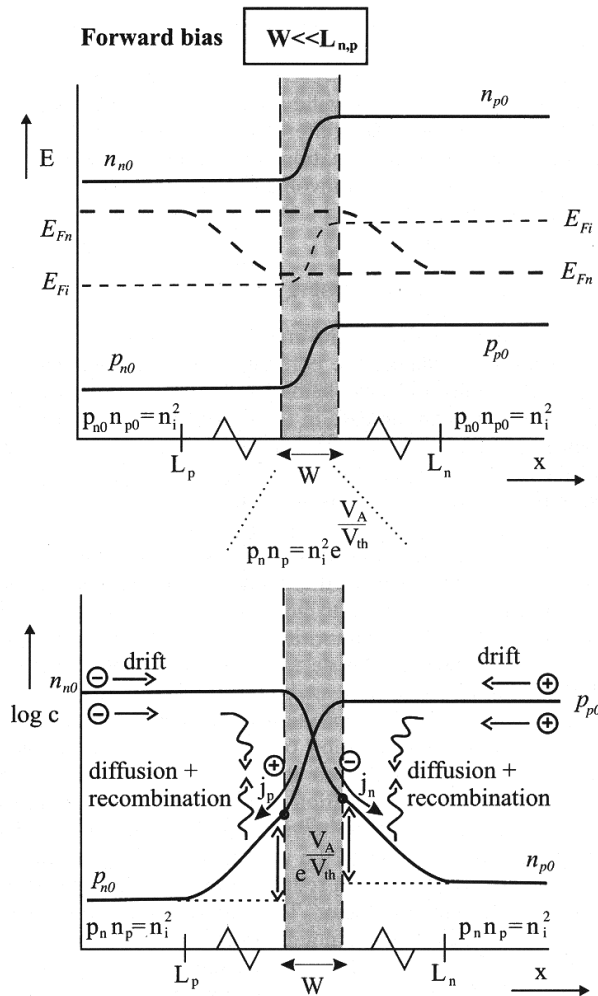
Diode karakterisiek

Fysische werking pn-junctie (1)



$$j_n = qD_n \frac{dn_p}{dx} + qn\mu_n E$$

Fysische werking pn-junctie (2)

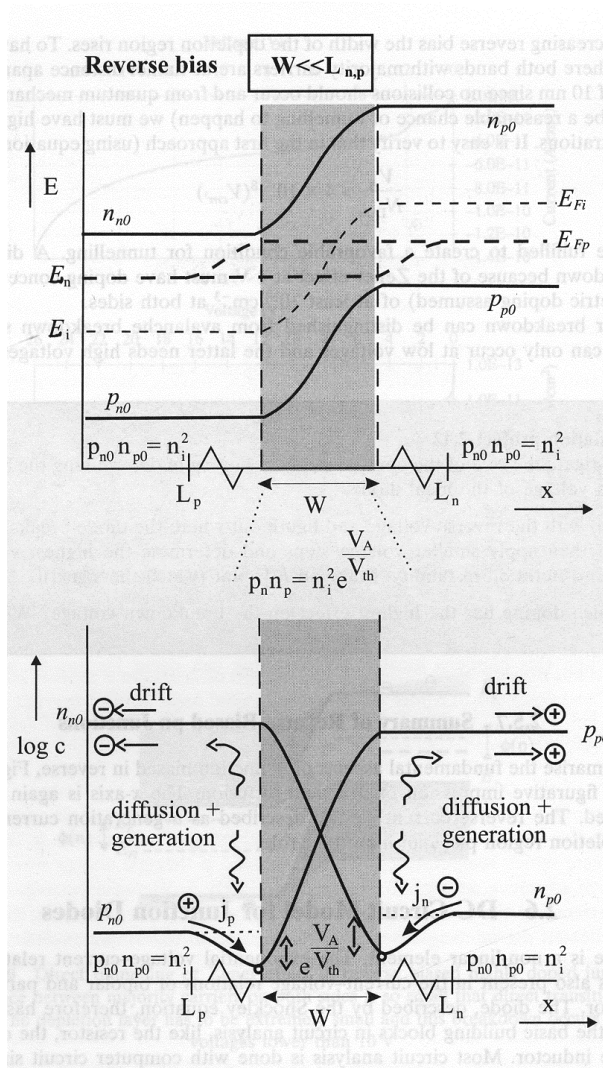


Voorwaartsstroom:

$$j = j_n + j_p = qn_i^2 \left[\frac{1}{N_A} \frac{D_n}{L_n} + \frac{1}{N_D} \frac{D_p}{L_p} \right] \left[\exp\left(\frac{qV_A}{kT}\right) - 1 \right]$$

$$j = j_0 \left[\exp\left(\frac{V_A}{V_{th}}\right) - 1 \right]$$

Fysische werking pn-junctie (3)

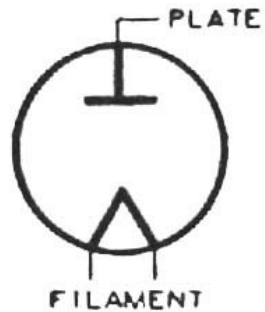


sperstroom

$$j = -j_0$$

$$j_0 = qn_i^2 \left[\frac{1}{N_A} \frac{D_n}{L_n} + \frac{1}{N_D} \frac{D_p}{L_p} \right]$$

Fleming Valve



Elektricit

Vacuum



J. A. FLEMING.

INSTRUMENT FOR CONVERTING ALTERNATING ELECTRIC CURRENTS INTO CONTINUOUS CURRENTS.

APPLICATION FILED APR. 18, 1905.

Fig.1.

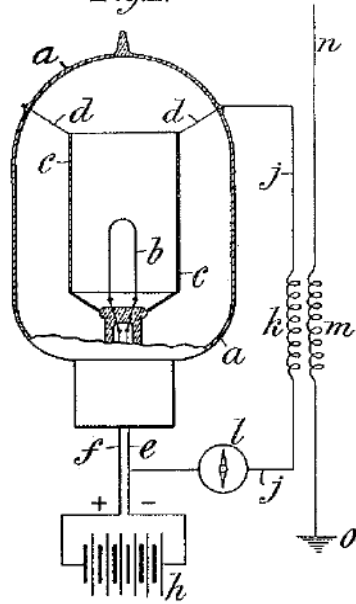


Fig.2.

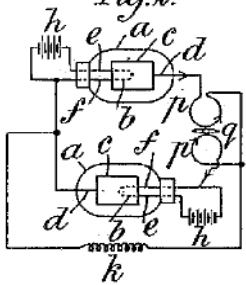
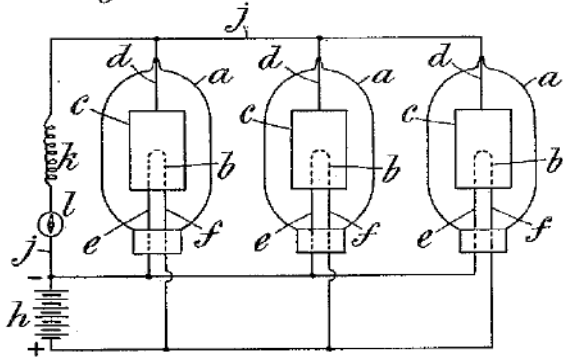


Fig.3.



Octrooi van Fleming: 1906, ingediend in 1904

Principe: Edison effect, beschreven in 1880



Vervolg: Lee de Forest, Audion, de triode (1908)

Witnesses

*William H. Davis.
James J. Cooper.*

Inventor

*John Ambrose Fleming
by his attorneys
Robt. S. S. Sheffield & Co.*

L. DE FOREST.
SPACE TELEGRAPHY.
APPLICATION FILED JAN. 29, 1907.

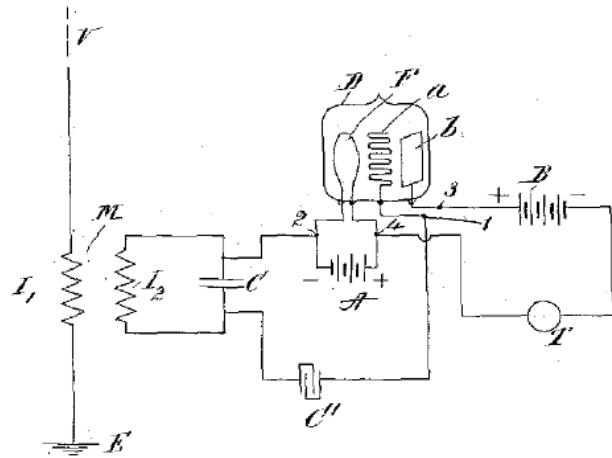


FIG. 1.



Lee de Forest 1906 (gefiled)

Met een sturelektrode werd versterking mogelijk en kon de elektronica ontwikkeld worden

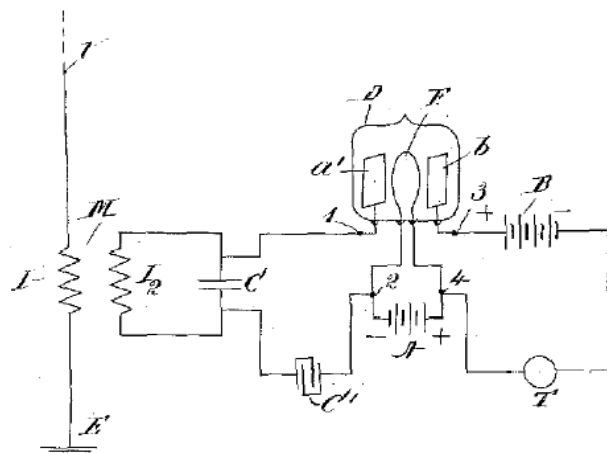


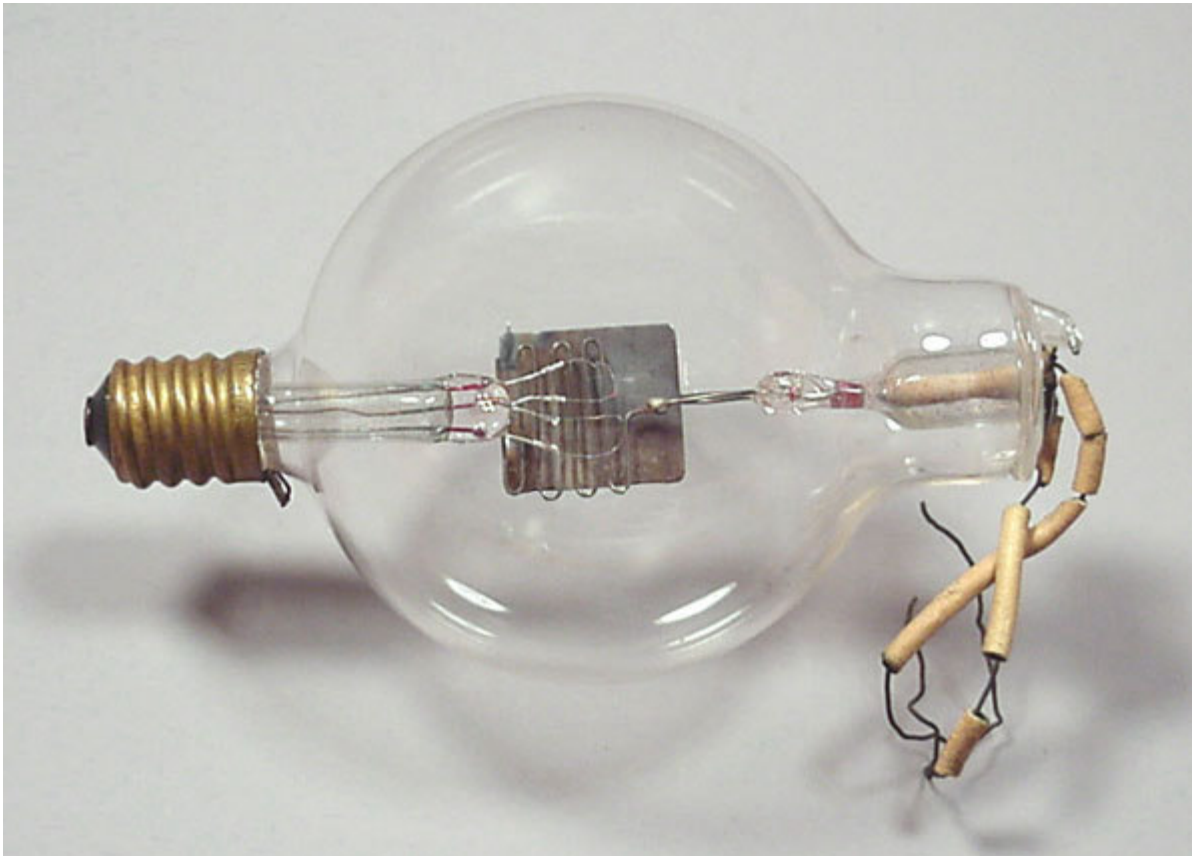
FIG. 2.

WITNESSES-
E. B. Tomlinson
Patrick J. Conroy

INVENTOR:
Lee de Forest
by Lee H. Woodworth,
Atty.

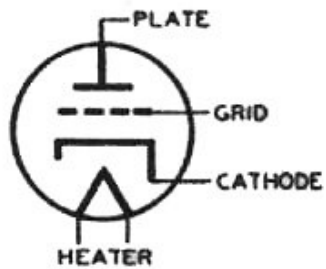
DeForest Spherical Audion

- DeForest Single Wing Audion c.1912
Tantalum Filaments

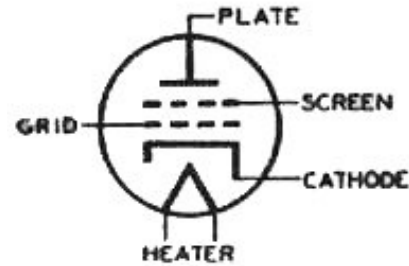


**“How does this
blamed thingy work?”**

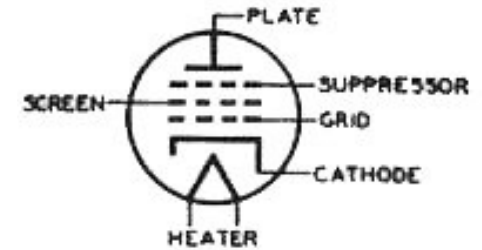
Vervolg vacuüm buizen



1907



1926



1929



Kathodestraalbuis: Karl Ferdinand Braun 1897
Televisie 1923

Natuurkunde vóór 1900

Gilbert	1544-1603	benoemt elektrostatische kracht (ηλεκτρον = barnsteen)
Coulomb	1736-1806	elektrische lading kwantificeerbaar (eenheid van lading) Coulombkracht
Watt	1736-1819	Stoommachine
Volta	1745-1827	depositie van lading bij elektrolyse, Voltacel
Ampère	1775-1836	onderlinge kracht stroomvoerende draden
Ørsted	1777-1851	wisselwerking tussen magneet en stroom (1820)
Ohm	1789-1854	eenheid van weerstand
Faraday	1791-1867	Materietransport bij elektrolyse (eenheid van capaciteit). Inductie (1831), elektrische en magnetische veldlijnen
Joule	1818-1889	stroomvoerende draad ontwikkelt warmte
Kirchhoff	1824-1887	serie en parallel stroomwetten
Maxwell	1831-1879	wiskundige formulering veldtheorie
Röntgen	1845-1923	Röntgenstralen, kristalstructuren (1901)
Lorentz	1853-1928	Lorentzkracht; verwevenheid deeltjes-golven (1902)

Natuurkunde na 1900

Planck	1858-1947	kwantumtheorie	1920
Rutherford	1871-1937	atoommodel;radioactieve straling	1908
Einstein	1879-1955	relativiteitstheorie	1921
Bohr	1885-1962	atoommodel	1922
Debije	1884-1966	molecuul- en kristalstructuren	1936
Schrödinger	1887-1961	kwantummechanica	1933
Heisenberg	1901-1976	kwantummechanica; onzekerheidsprincipe	1932
Dirac	1902-1982	Kwantummechanica; golfvergelijking	1933

Octrooien 19e eeuw

1837	Thomas Davenport	Electric motor
1839	Samuel Colt	Revolver
1840	Samuel F.B. Morse	Telegraph
1855	Isaac Singer	Sewing Machine
1869	Leigh Burton	Elec. resistance heater
1872	William Robinson	Elec. train signaling
1873	Louis Pasteur	Pasteurization
1873	Thomas Edison	Improved telegraph
1873	Louis Pasteur	Yeast process
1876	Alexander Graham Bell	Telephone
1879	Charles Brush	Carbon arc light
1880	Thomas Edison	Electric light

Octrooien eind 19e eeuw

1876	Alexander Graham Bell	Telephone
1880	Thomas Edison	Electric light
1884	George Eastman	Photographic film
1886	Elihu Thomson	Electric welding
1887	Carl Gassner	Dry cell battery
1888	Nikola Tesla	AC synchronous motor
1888	Nikola Tesla	Alternating current transmission
1888	Nikola Tesla	Electric distribution
1890	Nikola Tesla	Electric generator
1895	Rudolf Diesel	Diesel engine
1897	Guglielmo Marconi	Wireless telegraph
1900	Nikola Tesla	Wireless transmission of electric power

Octrooien begin 20e eeuw

Nov. 13,1900	Valdemar Poulsen	Magnetic tape recording
June 4, 1901	Guglielmo Marconi	Wireless telegraphy
Nov. 5, 1901	Henry Ford	Automobile
Sept. 30,1902	Thomas Edison	Motion picture camera
June 28,1904	Guglielmo Marconi	Wireless telegraph equip.
Nov. 15,1904	King Gillette	Gillette safety blade & razor
Nov. 7,1905	John Fleming	Two element vacuum tube
Dec. 6,1906	Denwoody	Wireless telegraphy system
May 22,1906	O. & W. Wright	Airplane
Nov. 13,1906	Lee de Forest	Radio tube detector
Jan. 15,1907	Lee de Forest	Radio amplifier tube
Feb. 18,1908	Lee de Forest	Triode
Dec. 7,1909	Leo Baekeland	Bakelite plastic

Vroege detector devices



galeniet

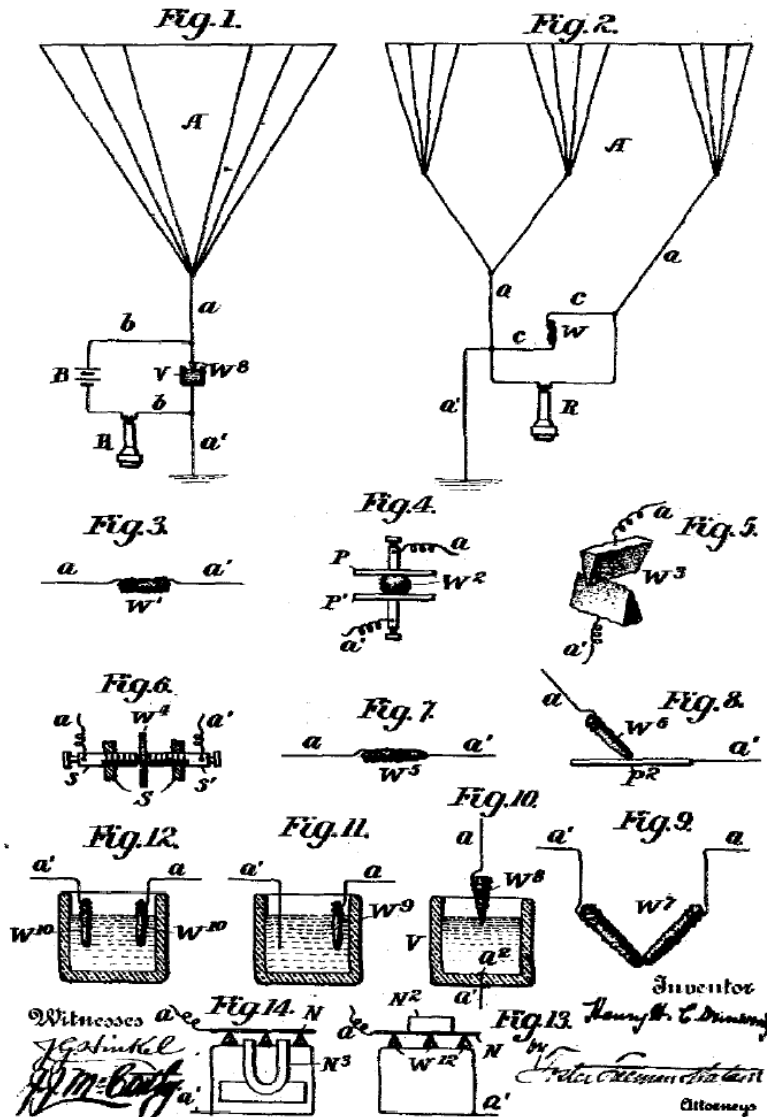
**Cats-whisker:
een metaaldraad contact
op een mineraal zoals bijv.
galeniet (PbS).**

**Voorlopers van de Schottky
diode of de puntcontact diode.
De werking werd niet begrepen**

Kristalradio's

H. H. C. DUNWOODY.
 WIRELESS TELEGRAPH SYSTEM.
 APPLICATION FILED MAR. 23, 1906.

Denwoody, 1906
 Draadloos telegrafie systeem

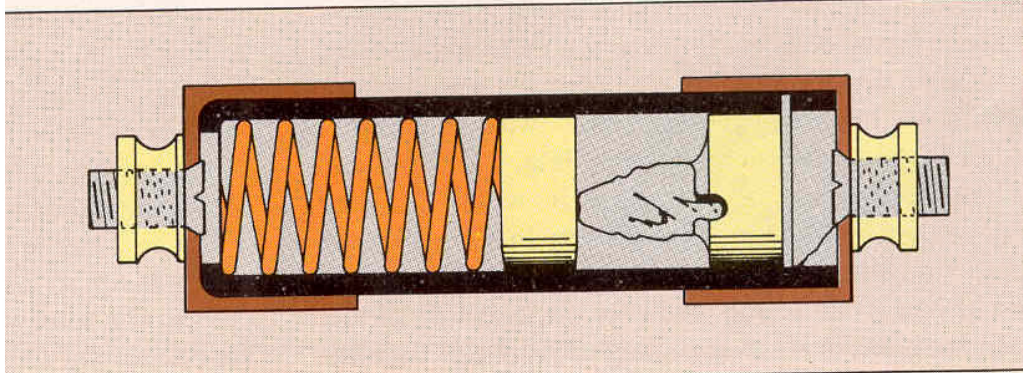


In Fig. 5 the wave-responsive device W^3 comprises two pieces or bodies of the crystalline material or carborundum having at least one relatively sharp edge, and the edges of the two pieces are placed in contact and may be supported in this relation in any suitable way, and are included in the circuit as before.

A Note on Carborundum.

To the Editors of Electrical World:

SIRS:—During an investigation of the unsymmetrical passage of current through a contact of carborundum and other substances a curious phenomenon was noted. On applying a potential of 10 volts between two points on a crystal of carborundum, the crystal gave out a yellowish light. Only one or two speci-



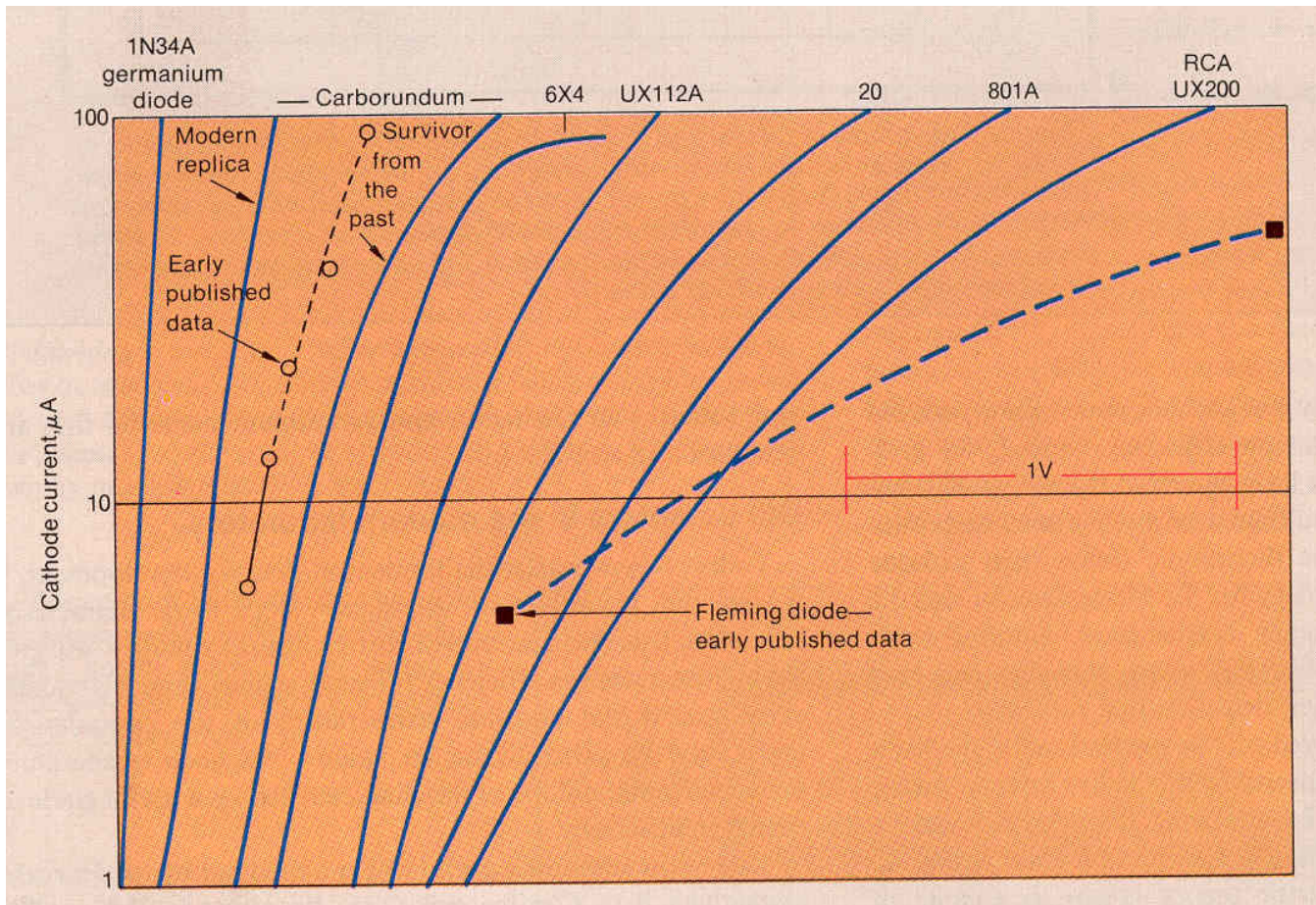
same section wherever the positive pole is placed.

There seems to be some connection between the above effect and the e.m.f. produced by a junction of carborundum and another conductor when heated by a direct or alternating current; but the connection may be only secondary as an obvious explanation of the e.m.f. effect is the thermoelectric one. The writer would be glad of references to any published account of an investigation of this or any allied phenomena.

NEW YORK, N. Y.

H. J. ROUND.

Fig. 1.1. Publication reporting on a “curious phenomenon”, namely the first observation of electroluminescence from a SiC (carborundum) light-emitting diode. The article indicates that the first LED was a Schottky diode rather than a p-n-junction diode (after H. J. Round, *Electrical World* **49**, 309, 1907).



Koolstof diodes waren in feite beter dan vacuum diode

Thackeray, When tubes beat crystals: early radio detectors ;IEEE Spectrum March 1983



Thackeray, When tubes beat crystals: early radio detectors ;IEEE Spectrum March 1983

A detector chronology

Date	Event	Frequency*
1874-83	Braun's crystal experiments	DC
1884	Edison's lamp diode	DC
1894	Elster and Geitel's phototube detector	Very high frequency
1899	Pupin's electrolytic detector	Up to 25 kHz
1903	Mercury-pool rectifier, Cooper-Hewitt	Power frequency
1903	Wehnelt's oxide-coated filament	No limit
1904	Fleming's "oscillation" valve	DC and high frequency
1905	De Forest's "Audion"	100 kHz
1906	Braun's psilomelan detector	
1906	Dunwoody's carborundum detector	
1906	Pickard's silicon detector	
1906	Brandes's theory of detection	
.	.	
.	.	
.	.	
.	.	
1945†	The IN34 germanium diode and its successors	

* Estimated
† In the preceding 40 years, progress was slow but more scientific, and steady engineering advances led to this milestone of the 1940s.

Thackeray, When tubes beat crystals: early radio detectors ;IEEE Spectrum March 1983

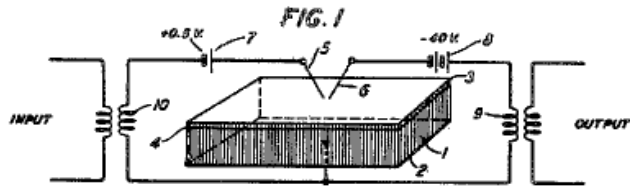
Oct. 3, 1950

J. BARDEEN ET AL.
THREE-ELECTRODE CIRCUIT ELEMENT UTILIZING
SEMICONDUCTIVE MATERIALS

2,524,035

Filed June 17, 1948

3 Sheets-Sheet 1



17 Juni 1948

Bardeen en Brattain octrooieren
separaat van Shockley

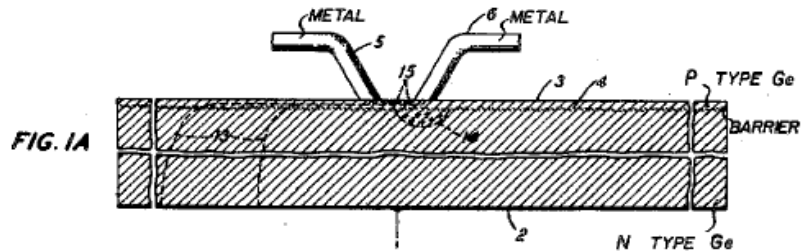


FIG. 2

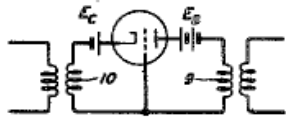


FIG. 10

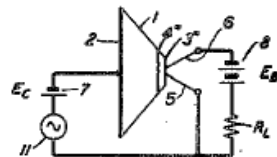


FIG. 11

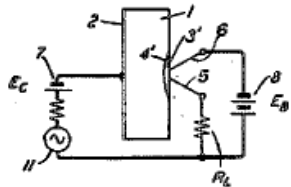
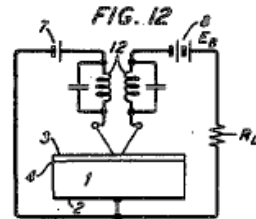


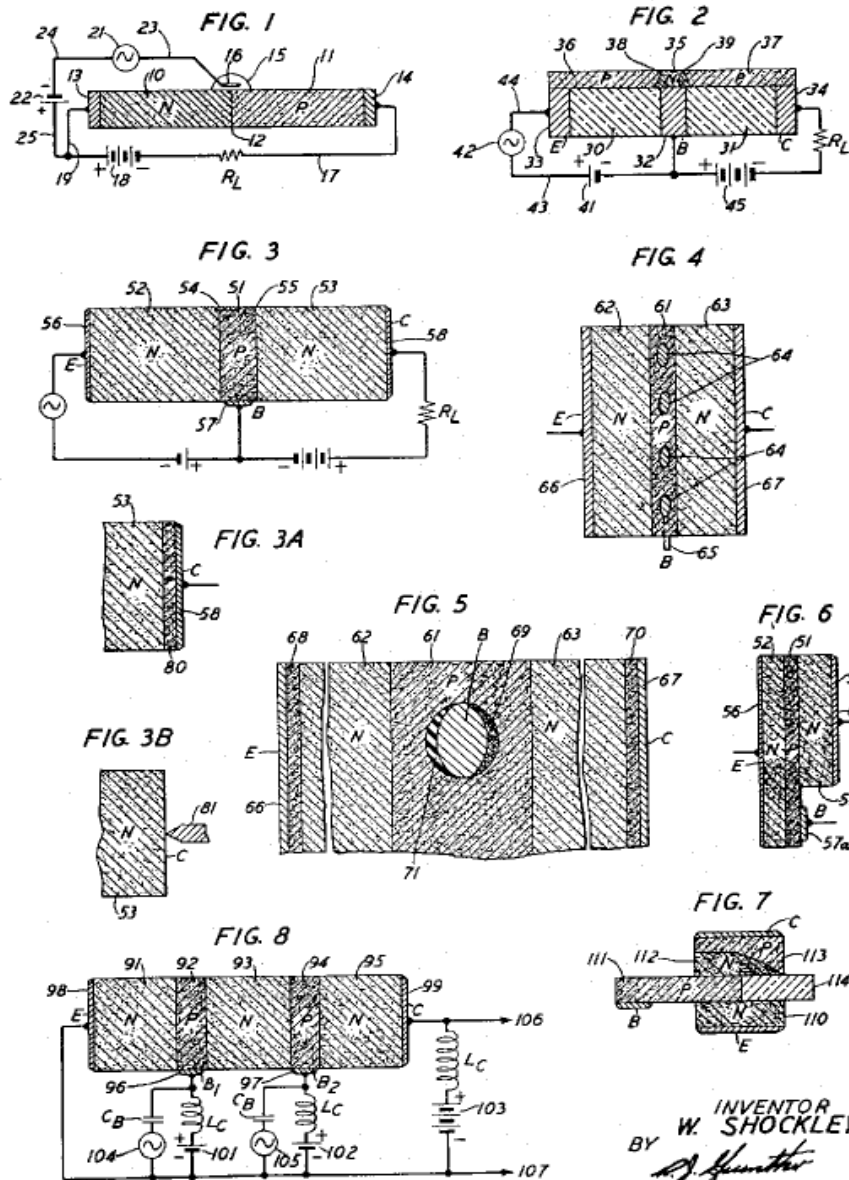
FIG. 12



INVENTORS: J. BARDEEN
W. H. BRATTAIN
BY *Harry C. Hart*
ATTORNEY

26 juni 1948

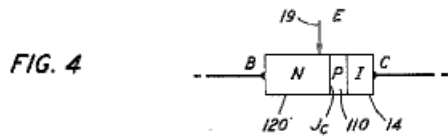
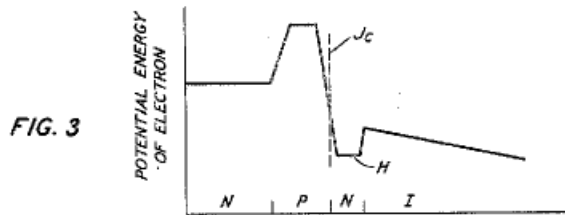
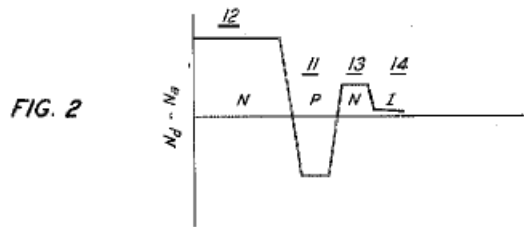
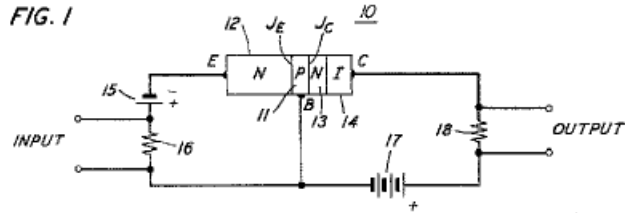
William Shockley octrooieert als eenling de junctietransistor



Another feature pertains to a semiconductive body comprising successive zones of material of opposite conductivity type each separated from the other by an electrical barrier, means for making external connection respectively to two of said zones, and means for making other connections intermediate to the two for controlling the flow of current across one or more of the electrical barriers.

Fig. 1 shows in section one embodiment of the invention with an appropriate circuit;

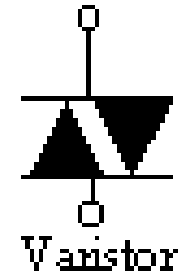
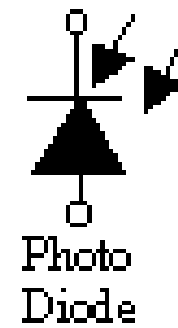
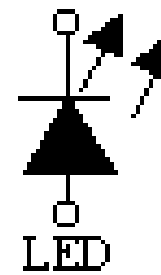
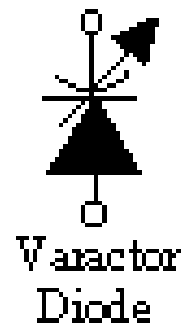
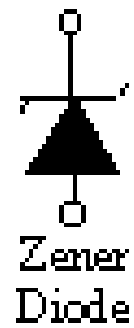
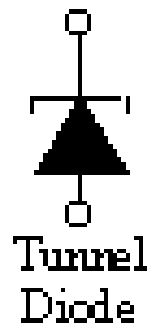
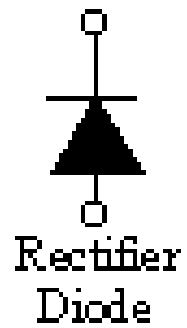
INVENTOR
W. SHOCKLEY
BY *[Signature]*
ATTORNEY



Shockley octrooieert diverse constructies (1951)

INVENTORS: W. SHOCKLEY
M. SPARKS
BY [Signature]
ATTORNEY

Diverse specialisaties



Integrated Circuit Complexity

Transistors
Per Die

10^{10}

10^9

10^8

10^7

10^6

10^5

10^4

10^3

10^2

10^1

10^0

1960

1965

1970

1975

1980

1985

1990

1995

2000

2005

2010

◆ 1965 Actual Data

■ MOS Arrays

▲ MOS Logic 1975 Actual Data

● 1975 Projection

■ Memory

▲ Microprocessor

1K

4K

16K

4004

8080

8086

64K

80286

256K

1M

i386™

i486™

4M

16M

64M

128M

256M

512M

1G

2G

4G

Pentium®

Pentium® II

Pentium® III

Pentium® 4

Itanium™

Halfgeleiderproductie in 2004:

Omzet: 150 miljard \$

10^{18} (1 miljard x 1 miljard) transistoren / jaar

150 miljoen transistoren / persoon.jaar

5 transistoren per seconde / persoon

In 100 jaar van buis naar nanotechnologie

